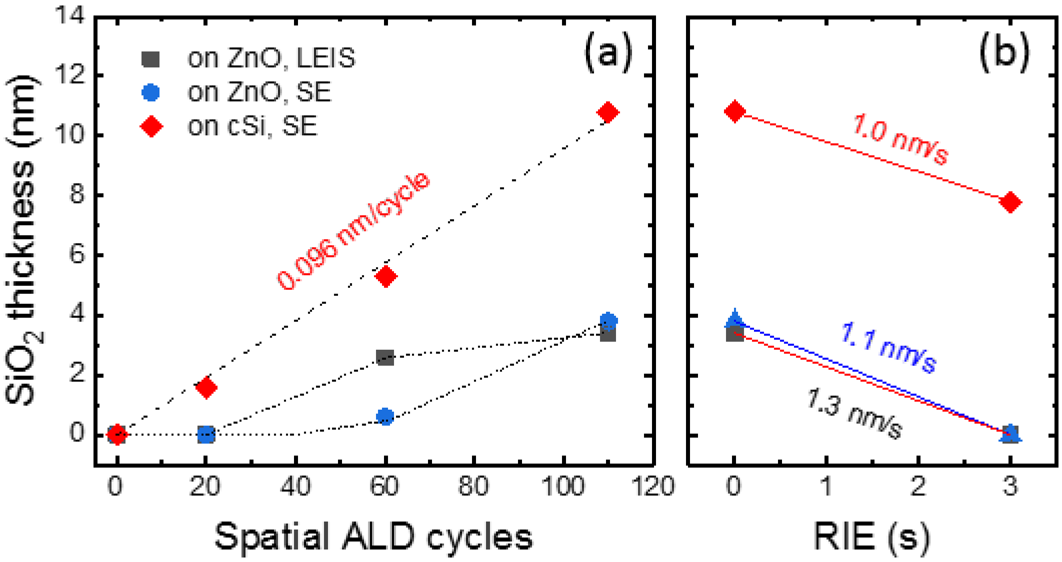

Figure 1. a) SiO_2 thickness as a function of the selective spatial ALD cycles for the first supercycle: (♦) on the growth area as measured by spectroscopic ellipsometry (SE); (●) on the non-growth area (ZnO) as measured by SE; (■) on the non-growth area as measured and by low energy ion spectroscopy, LEIS. b), SiO_2 thickness values after a 3 seconds reactive ion etching correction step.